



Serial No.: 57810-076

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of : Customer Number: 20277
Daijiro INOUE, et al. : Confirmation Number: 2234
Serial No.: 10/663,714 : Group Art Unit: 2811
Filed: September 17, 2003 : Examiner:
For: NITRIDE-BASED SEMICONDUCTOR LIGHT-EMITTING DEVICE

INFORMATION DISCLOSURE STATEMENT

Mail Stop IDS
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P.O. Box 1450
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Dear Sir:

In accordance with the provisions of 37 C.F.R. 1.56, 1.97 and 1.98, the attention of the Patent and Trademark Office is hereby directed to the documents listed on the attached form PTO-1449. It is respectfully requested that the documents be expressly considered during the prosecution of this application, and that the documents be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

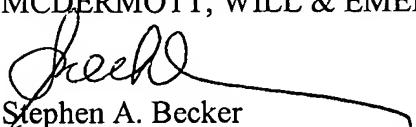
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Serial No.:

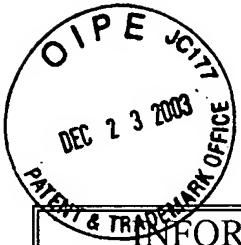
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Respectfully submitted,

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SHEET 1 OF 1

**INFORMATION DISCLOSURE
CITATION IN AN
APPLICATION**

(PTO-1449)

ATTY. DOCKET NO.
57810-076SERIAL NO.
10/663,714APPLICANT
Daijiro INOUE, et al.FILING DATE
September 17, 2003GROUP
2811**U.S. PATENT DOCUMENTS**

EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Code ₂ (<i>if known</i>)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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FOREIGN PATENT DOCUMENTS

EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document Country Codes-Number & Kind Codes (<i>if known</i>)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Figures Appear	Translation	
						Yes	No
		JP 2001-60720 A	03/06/2001	TOSHIBA CORP.		JAPAN (w/English Abstract)	
		JP 2002-124737	04/26/2002	SANYO ELECTRIC CO LTD		JAPAN (w/English Abstract)	
		JP 2002-299768	10/11/2002	MATSUSHITA ELECTRIC IND CO LTD		JAPAN (w/English Abstract)	
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		JP 11-340580	12/10/1999	FUJITSU LTD		JAPAN (w/English Abstract)	
		JP 10-294529	11/4/1998	TOSHIBA CORP.		JAPAN (w/English Abstract)	

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	
		T. Asano, et al. " High-power 400-nm-band AlGaN-based laser diodes with low aspect ratio." Applied Physics Letters, Volume 80, Number 19, May 13, 2002, pp.3497-3499	
		Nishinaga Tatau, " Hetero-epitaxy with Large Lattice Mismatch and Microchannel Epitaxy of Compound Semiconductor." Department of Electronic Engineering, Graduate School of Engineering, Volume 21, No. 6, pp. 320-325, 2000	
		Takashi Mizuno, et al. " High power Blue-violet Laser Diodes." The Institute of Electronics, Information and Communication Engineers, Technical Report of IEICE. ED2002-112, LQE2002-87 (2002-06), pp. 63-66	
		H. Amano, et al. " Metalorganic vapor phase epitaxial growth of a high quality GaN film using an AlN buffer layer." Appl. Phys. Lett., Vol. 48, No. 5, 3 February 1986, pp. 353-355	

EXAMINER

DATE CONSIDERED

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